



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Sheu, et al. Docket No.: TSM03-0140  
Serial No.: 10/619,828 Art Unit: 2811  
Filed: July 15, 2003 Examiner: TBD  
For: Self-Aligned MOSFET having an Oxide Region below the Channel

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IDS Forms PTO/SB/08a and 08b (3 pages) citing (41) references  
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Respectfully submitted,

*Natalie Swider*

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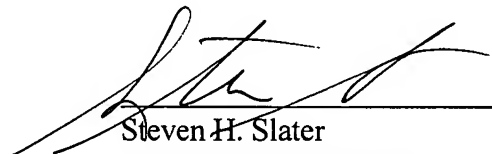
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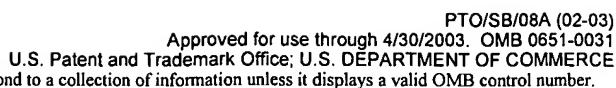
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Respectfully submitted,

25 MAR 2004  
Date

  
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|   |   |    |   | Application Number       | 10/619,828   |
| <b>INFORMATION DISCLOSURE<br/>STATEMENT BY APPLICANT</b><br>(use as many sheets as necessary) |   |    |   | Filing Date              | 07/15/2003   |
|   |   |    |   | First Named Inventor     | Sheu, et al. |
|   |   |    |   | Group Art Unit           | 2811         |
|   |   |    |   | Examiner Name            | TBD          |
|   |   |    |   | Attorney Docket Number   | TSM03-0140   |
| Sheet   | 2 | of | 3 |                          |              |

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|  | 18        | ISMAIL, K, <i>et al.</i> , "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letters, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.   |                 |
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|  | 31        | MATTHEWS, J.W., et al., "Defects in Epitaxial Multilayers - III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.   |                 |
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